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**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listings of Claims:**

Claim 1: (currently amended) A method of operating a deposition process chamber, the method comprising:

placing a substrate in said process chamber;

depositing a film on said substrate, said depositing leaving a deposition residue on an interior surface of said chamber; and

cleaning said deposition residue from said interior surface by creating a fluorine-containing plasma in said chamber, said fluorine-containing plasma leaving a fluorine-containing contaminant on said interior surface; and thereafter removing said fluorine-containing contaminant by

supplying an oxygen-containing gas into the process chamber;

supplying a hydrogen-containing gas into the process chamber, said hydrogen-containing gas being different from said oxygen-containing gas and being selected from a group consisting of NH<sub>3</sub> and H<sub>2</sub>;

producing a plasma comprising of a mixture of the oxygen-containing gas and the hydrogen-containing gas, thereby exothermically producing H<sub>2</sub>O;

causing so that the plasma to react reacts with the fluorine-containing contaminant to form a fluorine-containing material; and

removing the fluorine-containing material from the process chamber.

Claim 2: (canceled)

Claim 3: (previously presented) The method of claim 1, wherein the oxygen-containing gas is selected from a group consisting of N<sub>2</sub>O, O<sub>2</sub> and air.

Claim 4: (canceled)

Claim 5: (previously presented) The method of claim 1, wherein producing the plasma produces an ion flux to an interior surface of the process chamber, so that the ion